



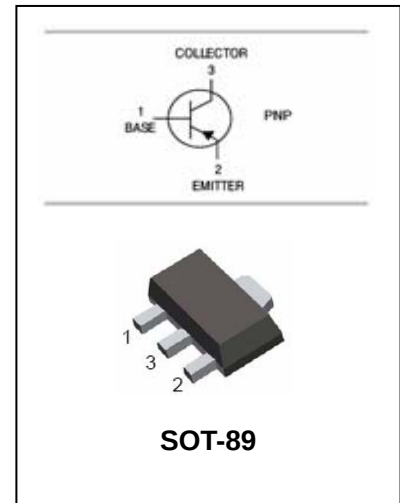
DONGGUAN NANJING ELECTRONICS LTD.,

PNP Silicon Epitaxial Planar Transistor

KTA1663

FEATURES

- 1W(Mounted on Ceramic Substrate).
- Small flat package.
- Complementary: KTC4375.



ORDERING INFORMATION

Type No.	Marking	Package Code
KTA1663	HO/HY	SOT-89

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-30	V
V_{CEO}	Collector-Emitter Voltage	-30	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-1.5	A
I_B	Base Current	-0.3	A
P_C	Collector Dissipation	500	mW
T_j, T_{stg}	Junction and Storage Temperature	-55 to +150	°C

PNP Silicon Epitaxial Planar Transistor

KTA1663

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-1mA, I_E=0$	-30			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-10mA, I_B=0$	-30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-1mA, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-30V, I_E=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5V, I_C=0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE}=-2V, I_C=-500mA$	100		320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-1.5A, I_B=-0.03A$			-2.0	V
Base-emitter voltage	V_{BE}	$V_{CE}=-2V, I_C=-500mA$			-1.0	V
Transition frequency	f_T	$V_{CE}=-2V, I_C=-500mA$		120		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$			50	pF

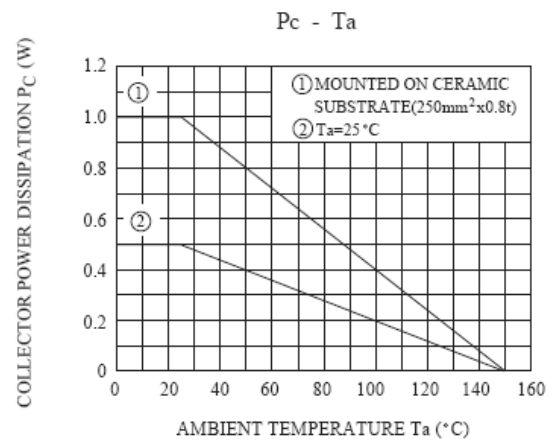
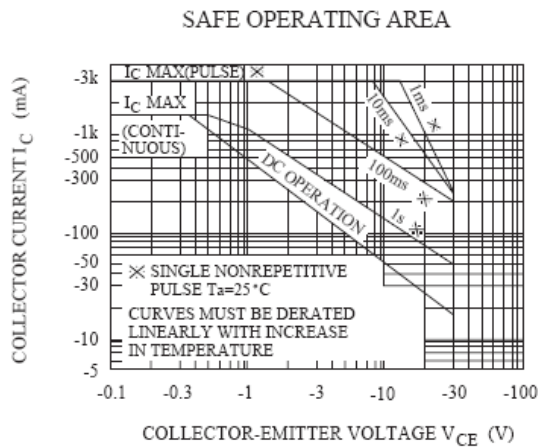
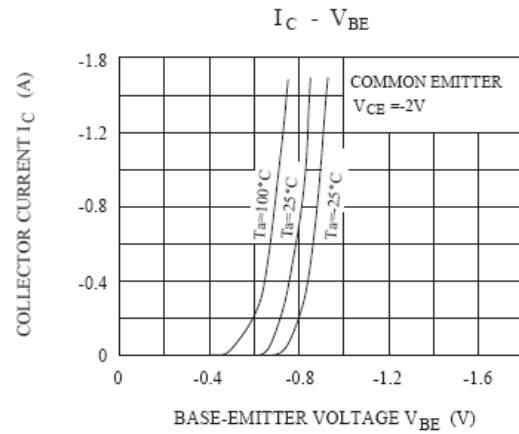
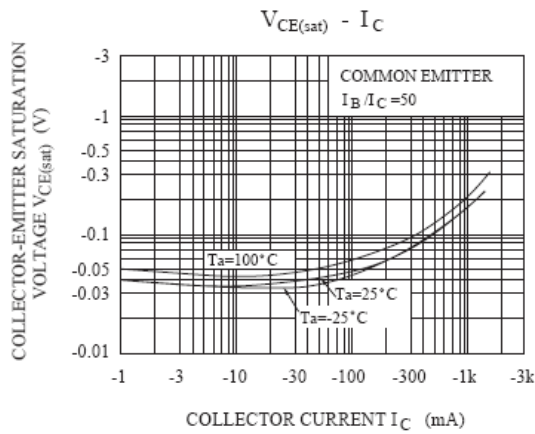
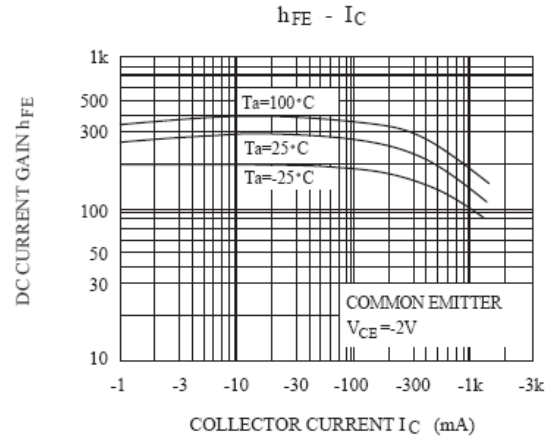
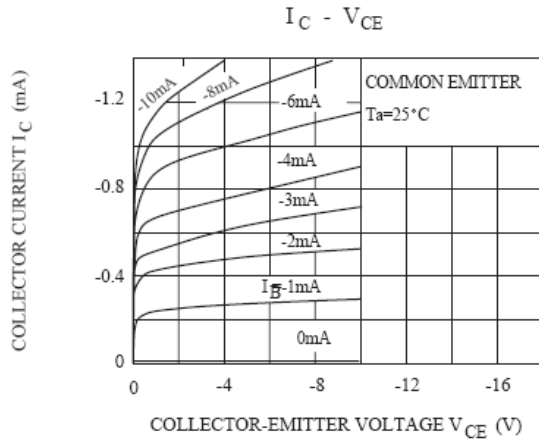
CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y
Range	100-200	160-320
MARKING	HO	HY

PNP Silicon Epitaxial Planar Transistor

KTA1663

TYPICAL CHARACTERISTICS @ $T_a=25^\circ\text{C}$ unless otherwise specified



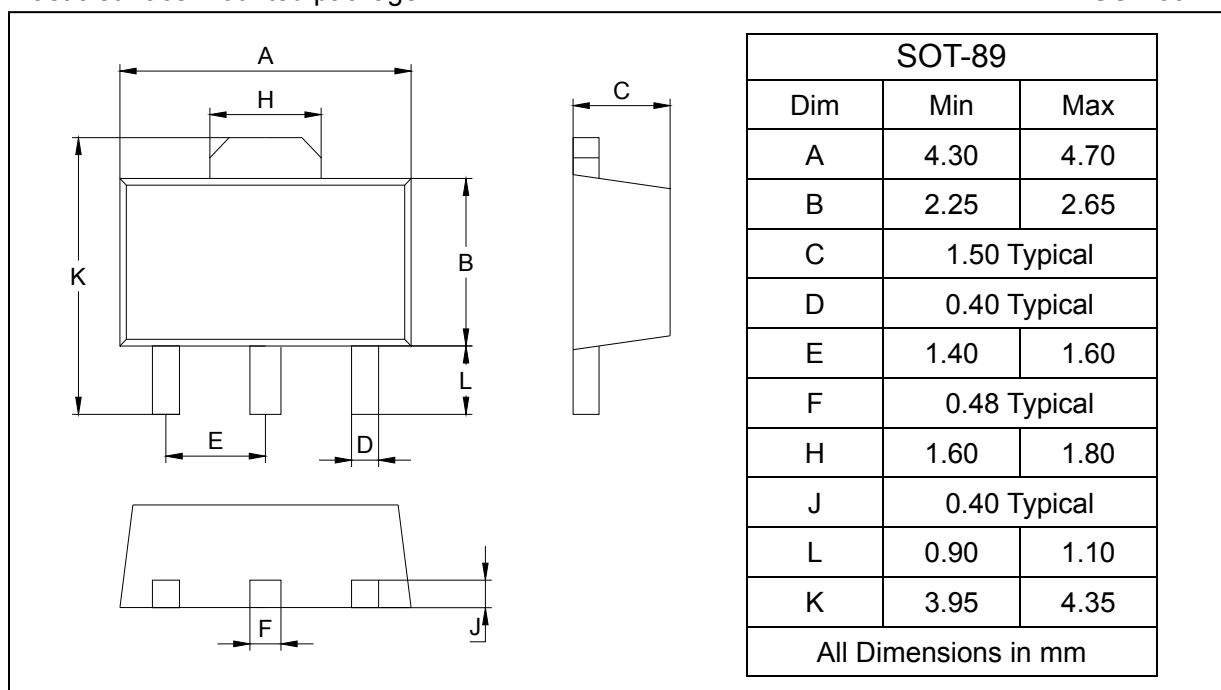
PNP Silicon Epitaxial Planar Transistor

KTA1663

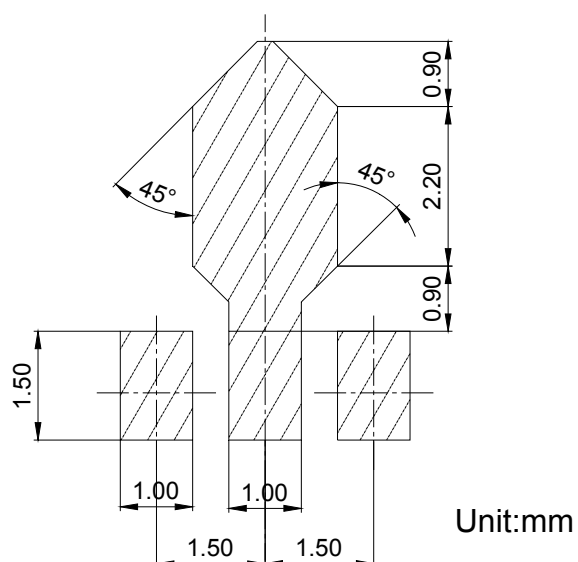
PACKAGE OUTLINE

Plastic surface mounted package

SOT-89



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
KTA1663	SOT-89	1000/Tape&Reel